



Attorney Docket: 040301/0578

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Nobutoshi AOKI et al.

Title: SEMICONDUCTOR INTEGRATED CIRCUIT INCLUDING  
INSULATED GATE FIELD EFFECT TRANSISTOR AND METHOD  
OF MANUFACTURING THE SAME

Appl. No.: 09/440,928

Filing Date: November 16, 1999

Examiner: S. Rao

Art Unit: 2814

**PROPOSED CHANGES TO THE DRAWINGS AND  
SUBMISSION OF CORRECTED FORMAL DRAWINGS**

Commissioner for Patents  
PO Box 1450  
Alexandria, Virginia 22313-1450

Sir:

Applicants propose to amend FIG 3 as shown in red on the attached copy of the drawing. A corrected formal drawing showing FIGS. 3(A) and 3(B) is also attached herewith.

Respectfully submitted,

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May 27, 2003 (Tuesday after holiday)

Date

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